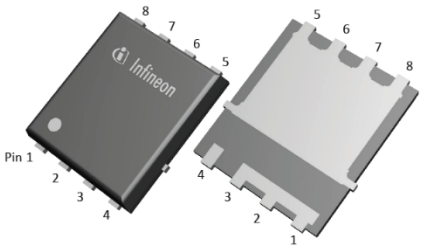
英飞凌MOSFET

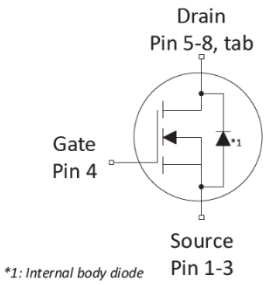
PG-TDSON-8

OptiMOS™ 6 功率晶体管，60 V



特性

- 针对低压驱动和电池供电应用进行了优化
- 针对高性能 SMPS 进行了优化
- N沟道，标准电平
- 极低的导通电阻 $R_{DS(on)}$
- 卓越的热阻
- 100% 雪崩测试
- 无铅镀层；符合 RoHS 标准
- 符合 IEC61249-2-21 标准的无卤素



产品验证

符合 JEDEC JESD47, JESD22 和 J-STD-020 相关测试的工业应用要求。

表 1　　主要性能参数

Parameter	Value	Unit
V_{DS}	60	V
$R_{DS(on),max}$	0.9	mΩ
I_D	344	A
Q_{oss}	137	nC
Q_G	97	nC
Q_{rr} (1000A/µs)	265	nC

Part number	Package	Marking	Related links
ISC009N06NM6	PG-TDSON-8	009N06N6	-

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目录

描述 1
最大额定值 3
热特性 4
电气特性 5
电气特性图 7
封装外形 11
修订记录 14
商标 15
免责声明 15

1 最大额定值

除非另有规定，T_A =25 °C

表 2 最大额定值

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Continuous drain current [1]	I_D	-	-	344	A	V_{GS}=10 V, T_C=25 °C
				243		V_{GS}=10 V, T_C=100 °C
				220		V_{GS}=8 V, T_C=100 °C
				40		V_{GS}=10V,T_A=25°C,R_{thJA}=50°C/W [2]
Pulsed drain current [3]	$I_{D,pulse}$	-	-	1376	A	T_C=25 °C
Avalanche energy, single pulse [4]	E_{AS}	-	-	579	mJ	I_D=50 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	221	W	T_C=25 °C
				3.0		T_A=25 °C, R_{thJA}=50 °C/W [2]
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	-

1) 额定值指产品仅具有数据手册指定的绝对最大值，保持外壳温度符合规定要求。其他外壳温度请参见图 2。需要根据实际环境条件降低额定值。

2) 器件置于40 mm × 40 mm × 1.5 mm 环氧树脂 PCB FR4 上，配有6 cm^2（单层，70 µm厚）铜层面积用于漏极连接。PCB在静止空气中垂直放置。

3) 详细信息请参见图 3

4) 详细信息请参见图 13

2 热特性

表 3 热特性

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	0.34	0.68	°C/W	-
Thermal resistance, junction - case, top	R_{thJC}		-	20		
Thermal resistance, junction - ambient, 6 cm^2 cooling area [5)]	R_{thJA}		-	50		

5) 器件置于40 mm × 40 mm × 1.5 mm 环氧树脂 PCB FR4基板上，配有6 cm^2（单层，70微米厚）铜层，用于漏极连接。PCB在静止空气中垂直放置。

3 电气特性

除非另有规定，T_j = 25°C

表 4 静态特性

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	2.1	2.7	3.3	V	V_{DS}=V_{GS}, I_D=118 µA
Zero gate voltage drain current	I_{DSS}	-	0.1	1.0	µA	V_{DS}=48 V, V_{GS}=0 V, T_j=25 °C
			10	100		V_{DS}=48 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	10	100	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	-	0.74	0.9	mΩ	V_{GS}=10 V, I_D=50 A
Drain-source on-state resistance [6]	$R_{DS(on)}$	-	0.82	1.1	mΩ	V_{GS}=8 V, I_D=25 A
Gate resistance	R_G	-	0.84	-	Ω	-
Transconductance [6]	g_{fs}	110	220	-	S	$\|V_{DS}\|\geq 2\|I_D\|R_{DS(on)max}$, I_D=50 A

[6] 由设计指定，未经过生产测试。

表 5 动态特性

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Input capacitance [7]	C_{iss}	-	6400	8300	pF	V_{GS}=0 V, V_{DS}=30 V, f=1 MHz
Output capacitance [7]	C_{oss}		2200	2900		
Reverse transfer capacitance [7]	C_{rss}		72	130		
Turn-on delay time	$t_{d(on)}$	-	13.5	-	ns	V_{DD}=30 V, V_{GS}=10 V, I_D=50 A, $R_{G,ext}$=1.6 Ω
Rise time	t_r		6.0			
Turn-off delay time	$t_{d(off)}$		32.9			
Fall time	t_f		8.5			

[7] 由设计指定，未经过生产测试。

表 6 栅极电荷特性 [8)]

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	28	-	nC	V_{DD}=30 V, I_D=50 A, V_{GS}=0 to 10 V
Gate charge at threshold	$Q_{g(th)}$		17.3	-	nC	
Gate to drain charge [9)]	Q_{gd}		20	30	nC	
Switching charge	Q_{sw}		31	-	nC	
Gate charge total [9)]	Q_g		97	121	nC	
Gate plateau voltage	$V_{plateau}$		4.3	-	V	
Output charge [9)]	Q_{oss}	-	137	182	nC	V_{DS}=30 V, V_{GS}=0 V

8) 参数定义请参数见“栅极电荷波形”

9) 由设计指定，未经过生产测试。

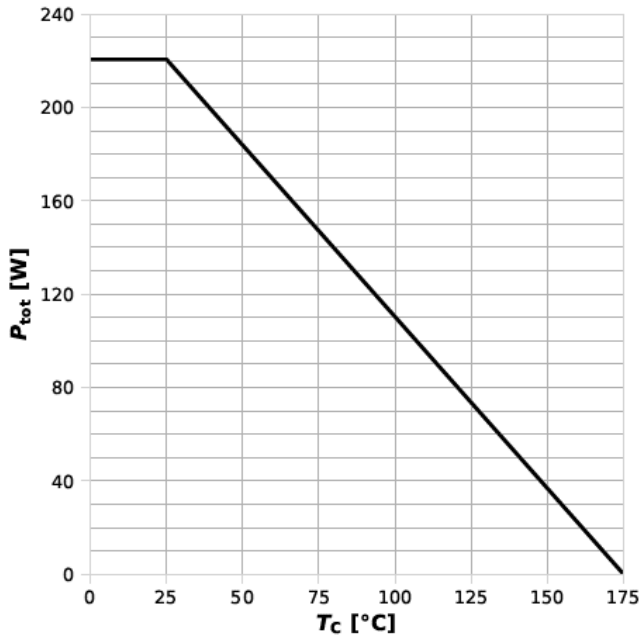
表 7 反向二极管

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	201	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$			1376		
Diode forward voltage	V_{SD}	-	0.79	1.0	V	V_{GS}=0 V, I_F=50 A, T_j=25 °C
Reverse recovery time [10)]	t_{rr}	-	51	102	ns	V_R=30 V, I_F=50 A, di_F/dt=100 A/µs
Reverse recovery charge [10)]	Q_{rr}		66	132	nC	
Reverse recovery time [10)]	t_{rr}	-	29	58	ns	V_R=30 V, I_F=50 A, di_F/dt=1000 A/µs
Reverse recovery charge [10)]	Q_{rr}		265	530	nC	

10) 由设计指定，未经过生产测试。

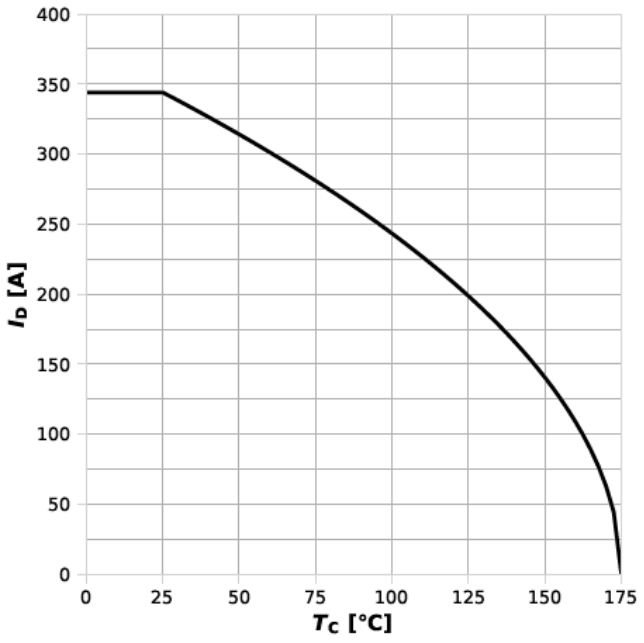
4 电气特性图

Diagram 1: Power dissipation



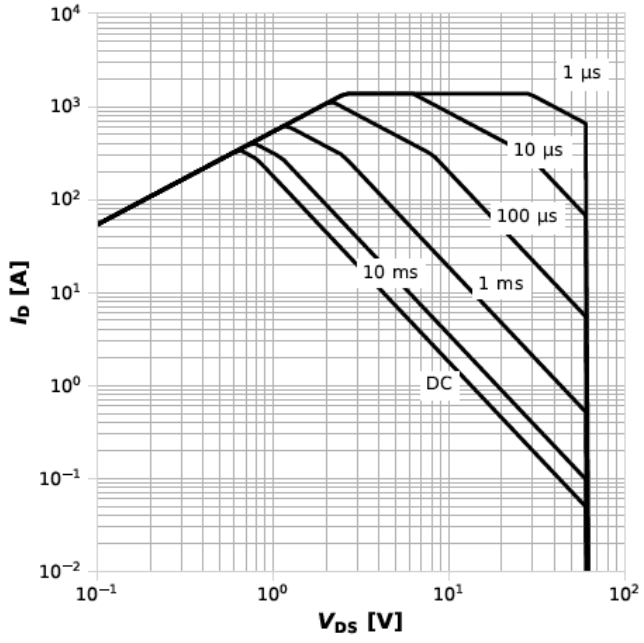
$P_{tot}=f(T_C)$

Diagram 2: Drain current



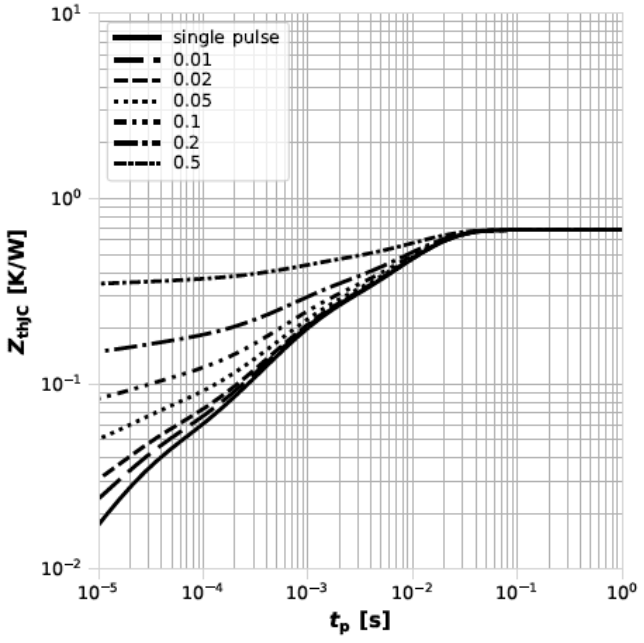
$I_D=f(T_C)$; $V_{GS}\geq 10$ V

Diagram 3: Safe operating area



$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$; parameter: t_p

Diagram 4: Max. transient thermal impedance



$Z_{thJC}=f(t_p)$; parameter: $D=t_p/T$

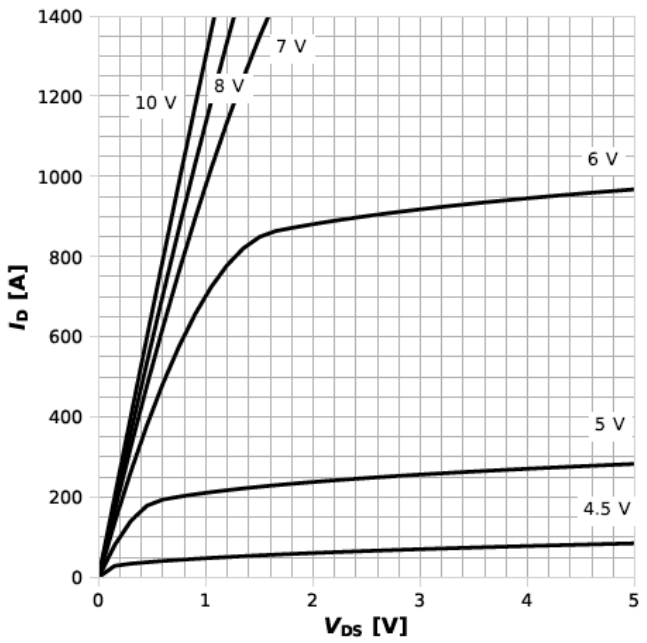
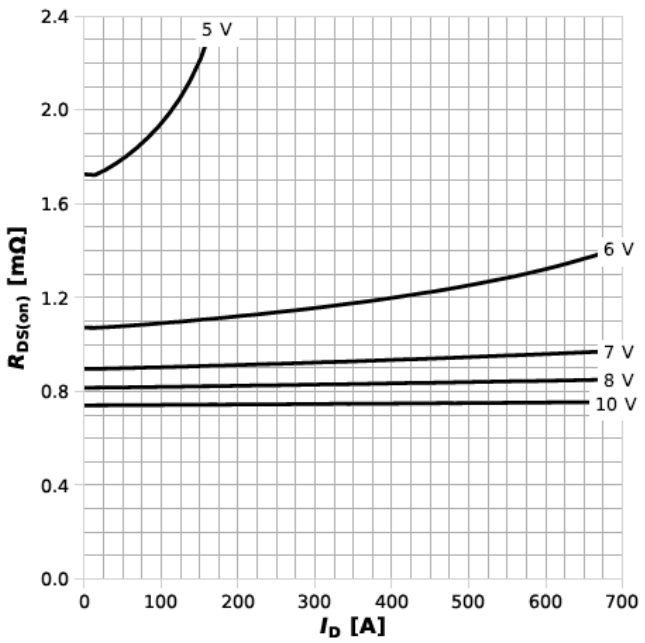
Diagram 5: Typ. output characteristics	Diagram 6: Typ. drain-source on resistance
	
$I_D=f(V_{DS})$, $T_j=25$ °C; parameter: V_{GS}	$R_{DS(on)}=f(I_D)$, $T_j=25$ °C; parameter: V_{GS}

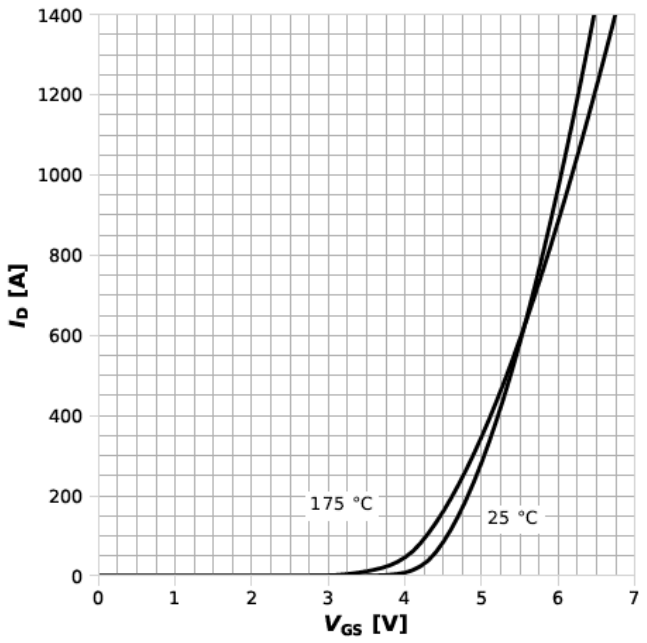
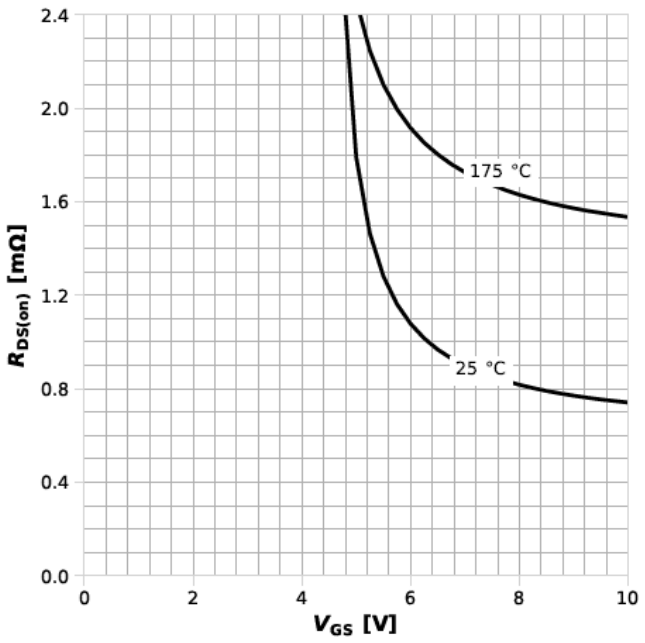
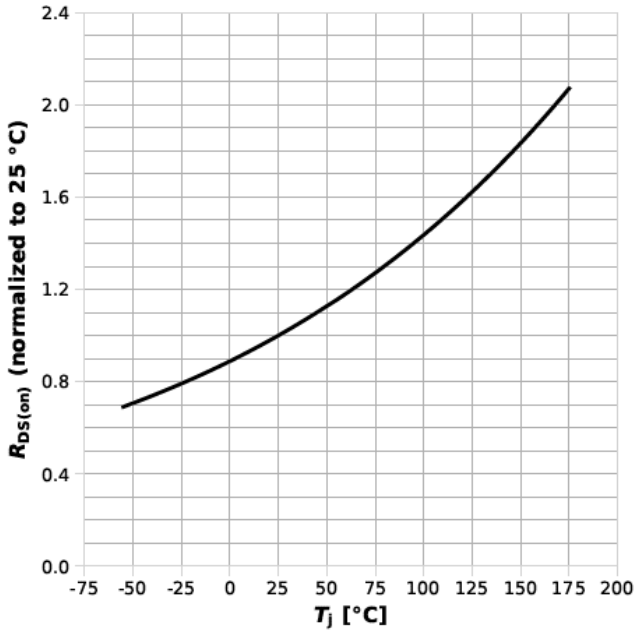
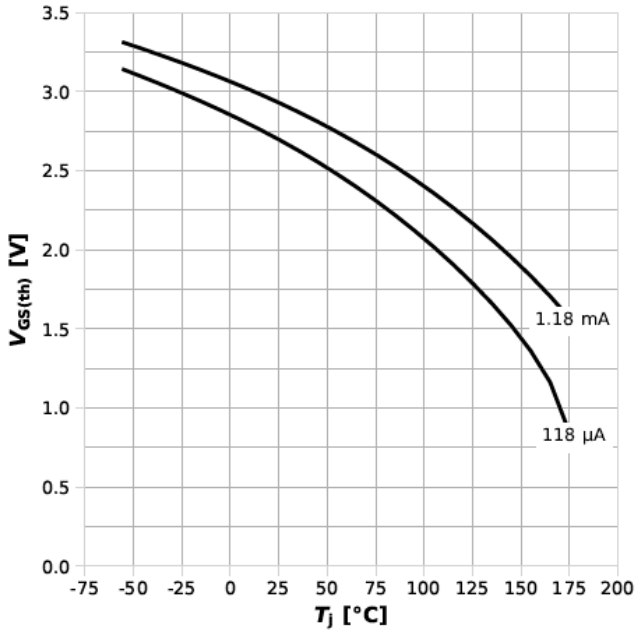
Diagram 7: Typ. transfer characteristics	Diagram 8: Typ. drain-source on resistance
	
$I_D=f(V_{GS})$, $\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$; parameter: T_j	$R_{DS(on)}=f(V_{GS})$, $I_D=50$ A; parameter: T_j

Diagram 9: Normalized drain-source on resistance



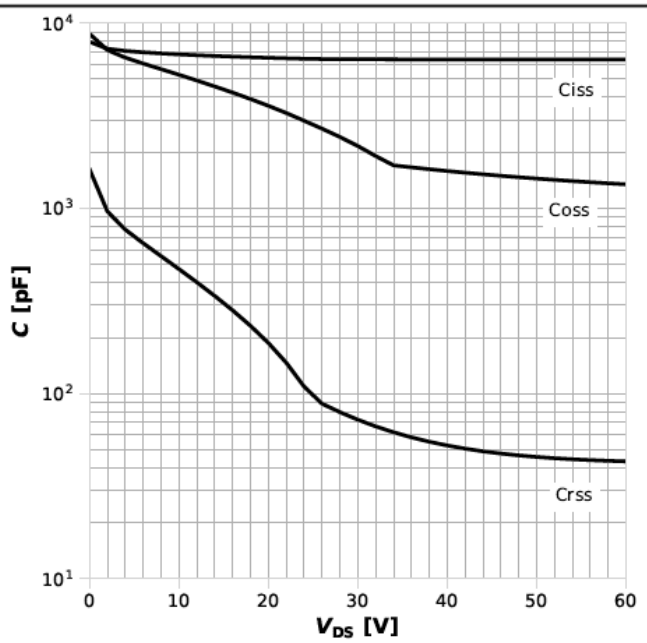
$R_{DS(on)}$=f(T_j), I_D=50 A, V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



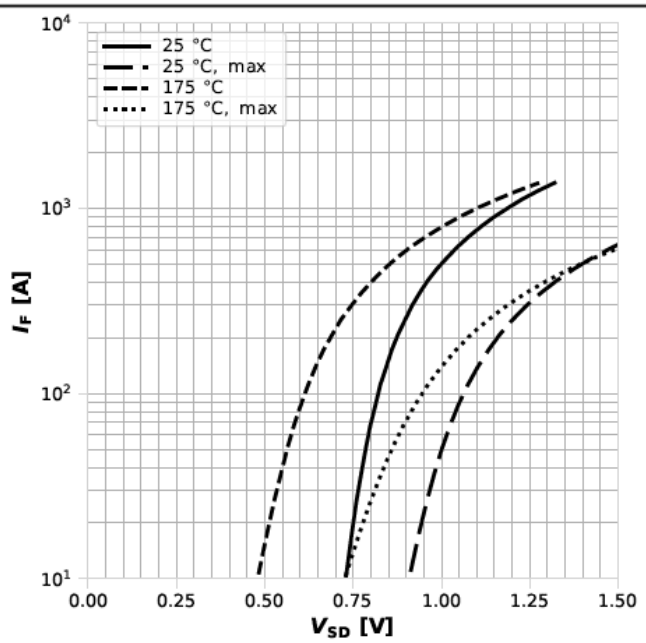
$V_{GS(th)}$=f(T_j), V_{GS}=V_{DS}; parameter: I_D

Diagram 11: Typ. capacitances



C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 12: Forward characteristics of reverse diode



I_F=f(V_{SD}); parameter: T_j

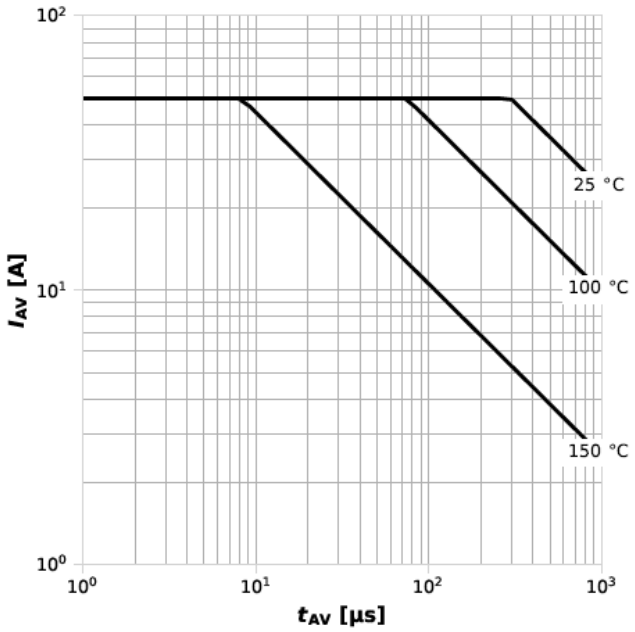
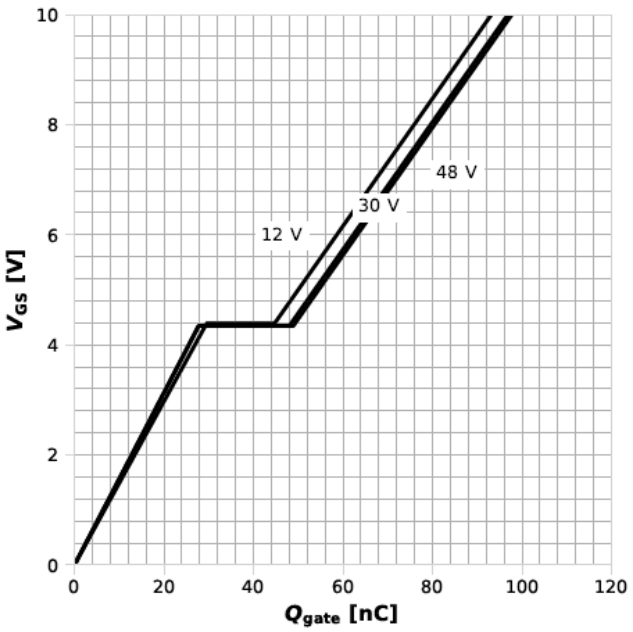
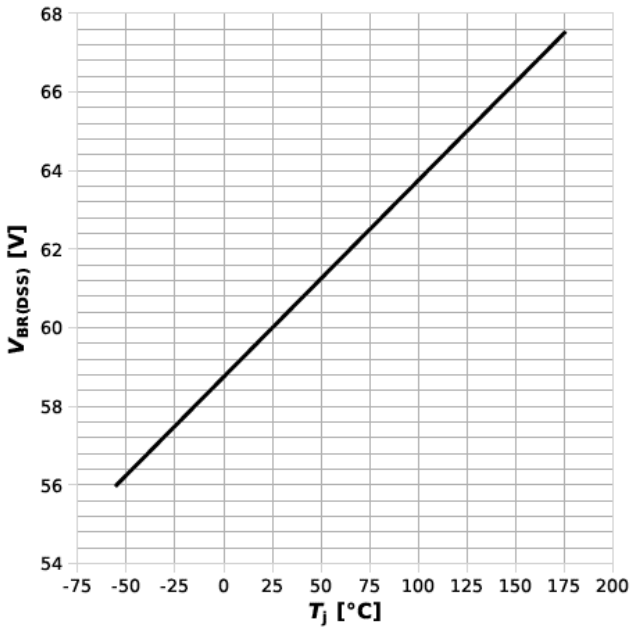
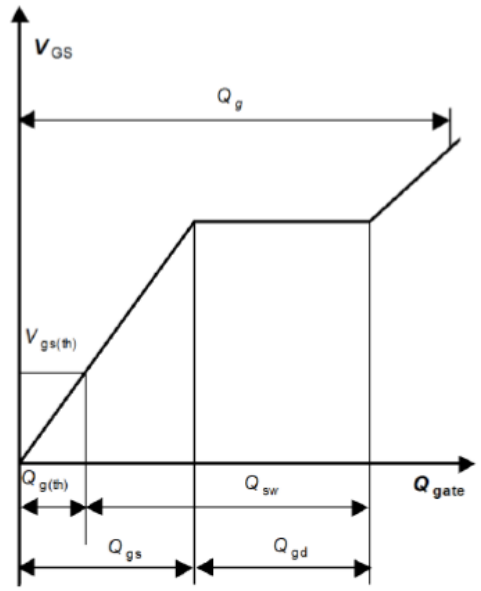
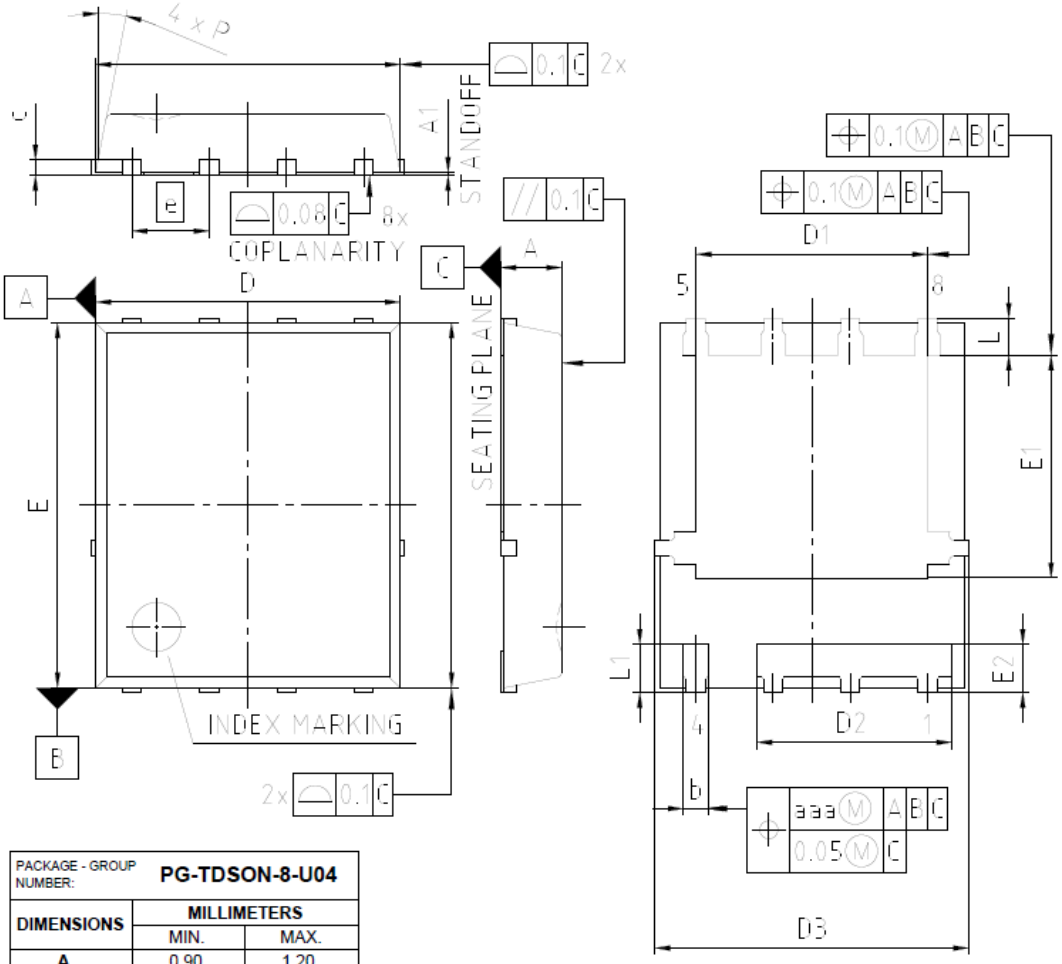
Diagram 13: Avalanche characteristics	Diagram 14: Typ. gate charge
	
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j,start}$	$V_{GS}=f(Q_{gate})$, $I_D=50$ A pulsed, $T_j=25$ °C; parameter: V_{DD}

Diagram 15: Min. drain-source breakdown voltage	Gate charge waveforms
	
$V_{BR(DSS)}=f(T_j)$; $I_D=10$ mA	-

5 封装外形



PACKAGE - GROUP NUMBER:	PG-TDSON-8-U04	
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	0.90	1.20
A1	0	0.05
b	0.26	0.54
c	0.15	0.35
D	4.80	5.35
D1	3.70	4.40
D2	2.94	3.25
D3	4.80	5.15
E	5.70	6.10
E1	3.40	3.76
E2	0.69	0.90
e	1.27	
L	0.45	0.72
L1	0.69	0.90
aaa	0.10	0.25
P	8°	12°

1) EXCLUDING MOLD FLASH
2) REMOVAL ON MOLD GATE
INTRUSION 0.1 MM
PROTRUSION 0.1 MM
3) LEAD LENGTH UP TO ANTI FLASH LINE
4) ALL METAL SURFACES ARE PLATED,
EXCEPT AREA OF CUT

图 1　　PG-TDSON-8 封装外形，尺寸单位为毫米

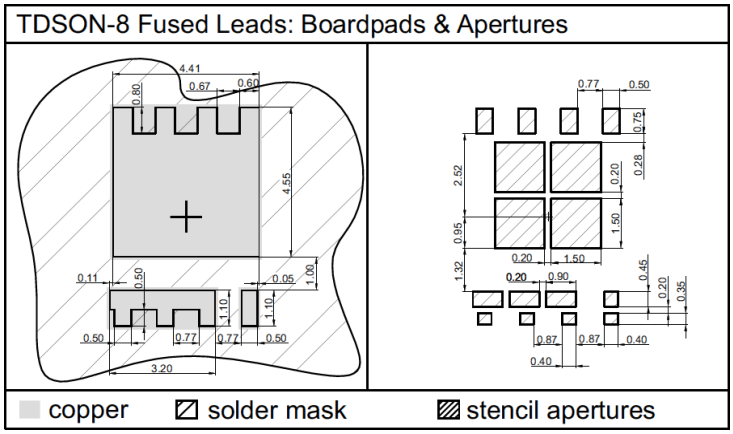


图 2　　PG-TDSON-8 封装图，尺寸单位为毫米

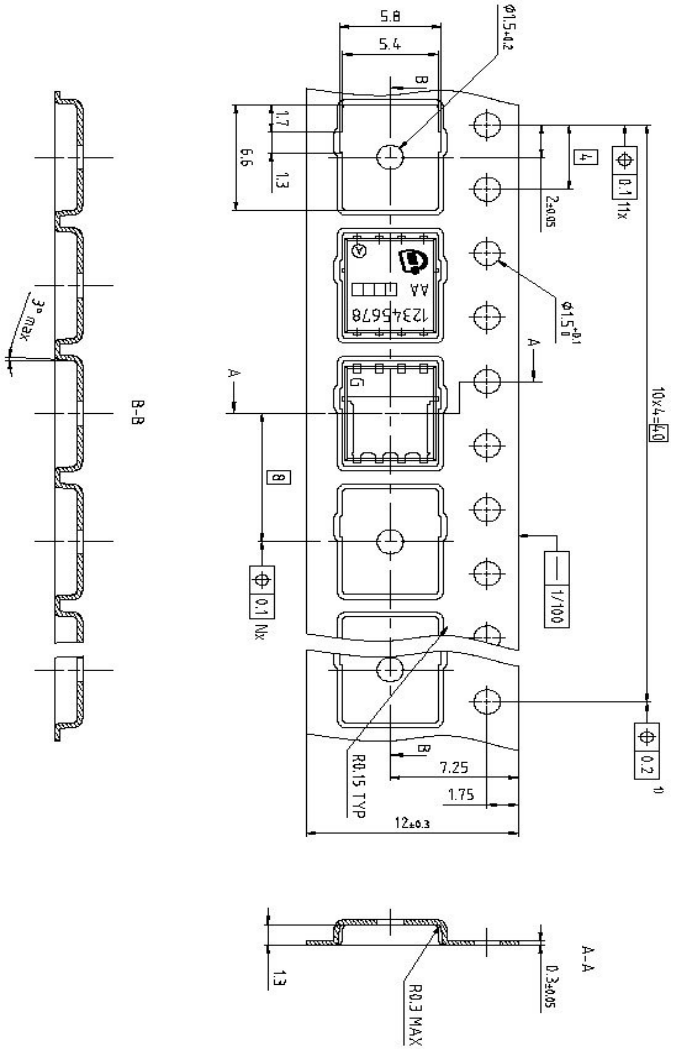


图 3　　PG-TDSON-8 封装变体，尺寸单位为毫米

修订记录

ISC009N06NM6

Revision 2025-07-07, Rev. 2. 1

Previous revisions

Revision	Date	Subjects (major changes since last revision)
2.0	2024-05-08	Release of final
2.1	2025-07-07	Revised Rdson at Vgs from 6V to 8V

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